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# AO4474

## 30V N-Channel MOSFET

### General Description

The AO4474 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge. This device is suitable for use as a high side switch in SMPS and general purpose applications.

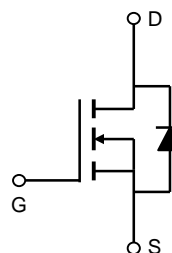
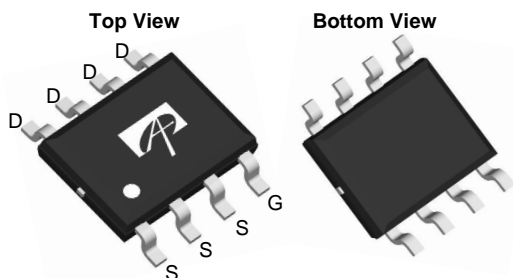
### Product Summary

$V_{DS}$  (V) = 30V  
 $I_D$  = 13.4A ( $V_{GS}$  = 10V)  
 $R_{DS(ON)} < 11.5m\Omega$  ( $V_{GS}$  = 10V)  
 $R_{DS(ON)} < 13.5m\Omega$  ( $V_{GS}$  = 4.5V)

100% UIS Tested  
 100% Rg Tested



SOIC-8



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>A, F</sup>	$T_A=25^\circ\text{C}$	13.4	A
	$T_A=70^\circ\text{C}$	10.7	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	60	
Power Dissipation	$T_A=25^\circ\text{C}$	3.7	W
	$T_A=70^\circ\text{C}$	2.4	
Avalanche Current <sup>B, G</sup>	$I_{AR}$	42	A
Repetitive avalanche energy 0.1mH <sup>B, G</sup>	$E_{AR}$	88	mJ
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	28	34	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	57	71
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	16	23	$^\circ\text{C/W}$

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**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V			0.1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	1	1.55	2.5	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	60			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =13.4A T <sub>J</sub> =125°C		9.5	11.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		11	13.5	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =13.4A		40		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.74	1.0	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		1210	1452	pF
C <sub>oss</sub>	Output Capacitance			330	396	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			85	119	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	0.8	1.2	1.6	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(10V)</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =13.4A		22	28	nC
Q <sub>g(4.5V)</sub>	Total Gate Charge			10	13	nC
Q <sub>gs</sub>	Gate Source Charge			3.7		nC
Q <sub>gd</sub>	Gate Drain Charge			2.7		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =1.1Ω, R <sub>GEN</sub> =3Ω		10		ns
t <sub>r</sub>	Turn-On Rise Time			6.3		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			21		ns
t <sub>f</sub>	Turn-Off Fall Time			2.8		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =13.4A, dI/dt=100A/μs		36	45	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =13.4A, dI/dt=100A/μs		47		nC
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =13.4A, dI/dt=500A/μs		20	27	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =13.4A, dI/dt=500A/μs		55		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

F: The current rating is based on the t ≤ 10s junction to ambient thermal resistance rating.

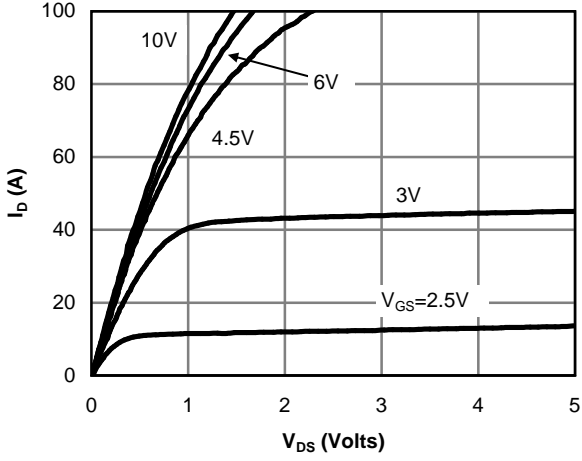
G: L=100uH, V<sub>DD</sub>=0V, R<sub>G</sub>=0Ω, rated V<sub>DS</sub>=30V and V<sub>GS</sub>=10V

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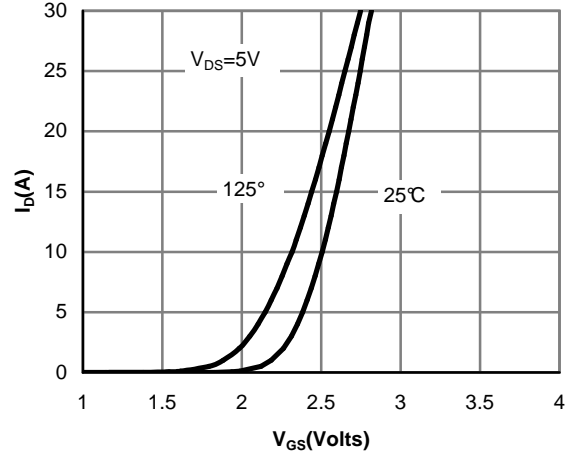
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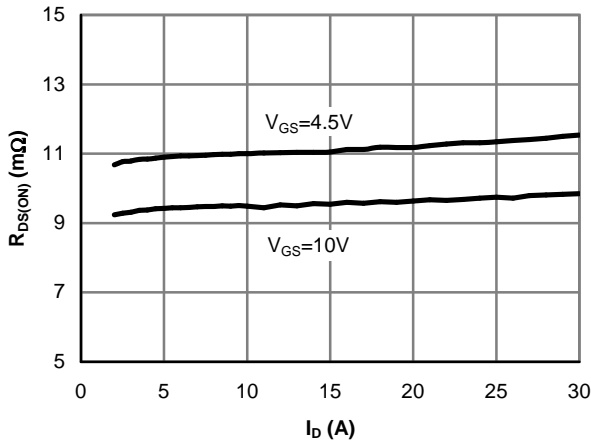
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



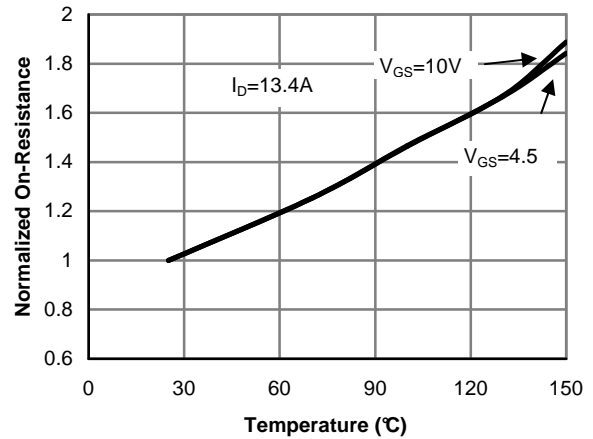
**Fig 1: On-Region Characteristics**



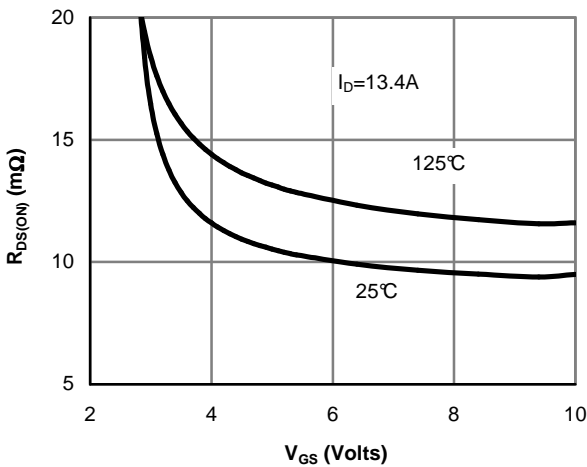
**Figure 2: Transfer Characteristics**



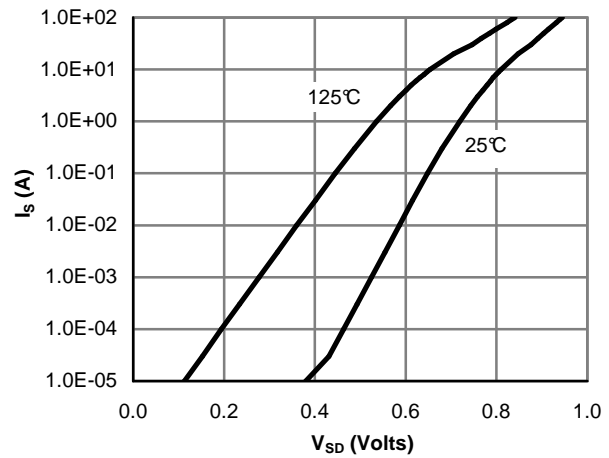
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**



**Figure 4: On-Resistance vs. Junction Temperature**



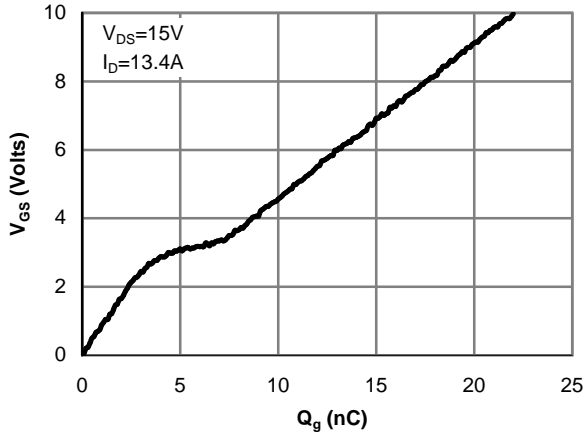
**Figure 5: On-Resistance vs. Gate-Source Voltage**



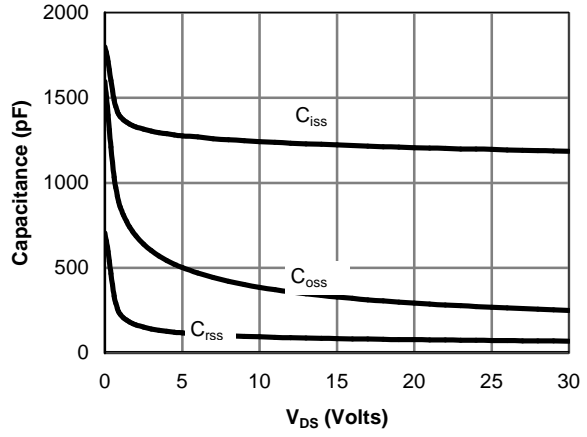
**Figure 6: Body-Diode Characteristics**

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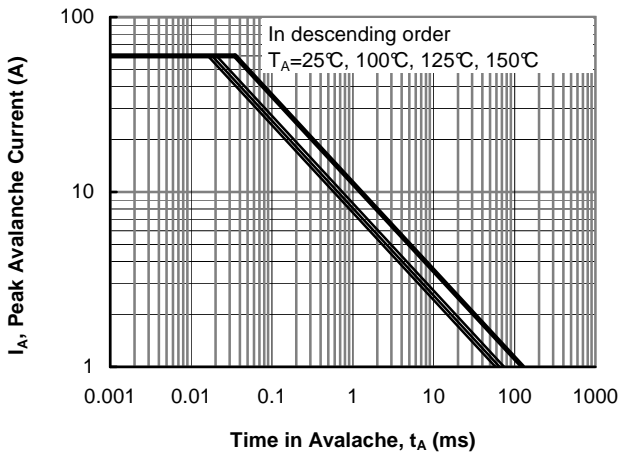
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



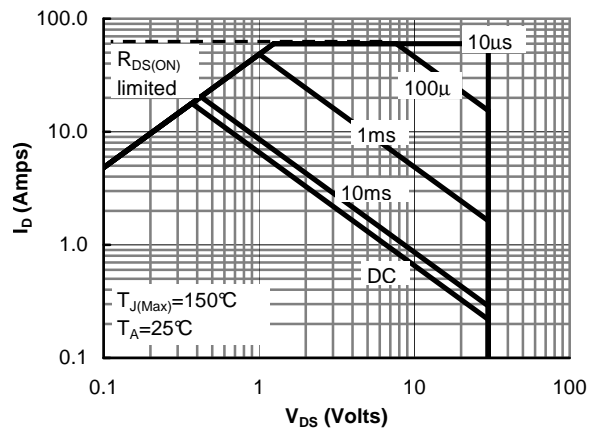
**Figure 7: Gate-Charge Characteristics**



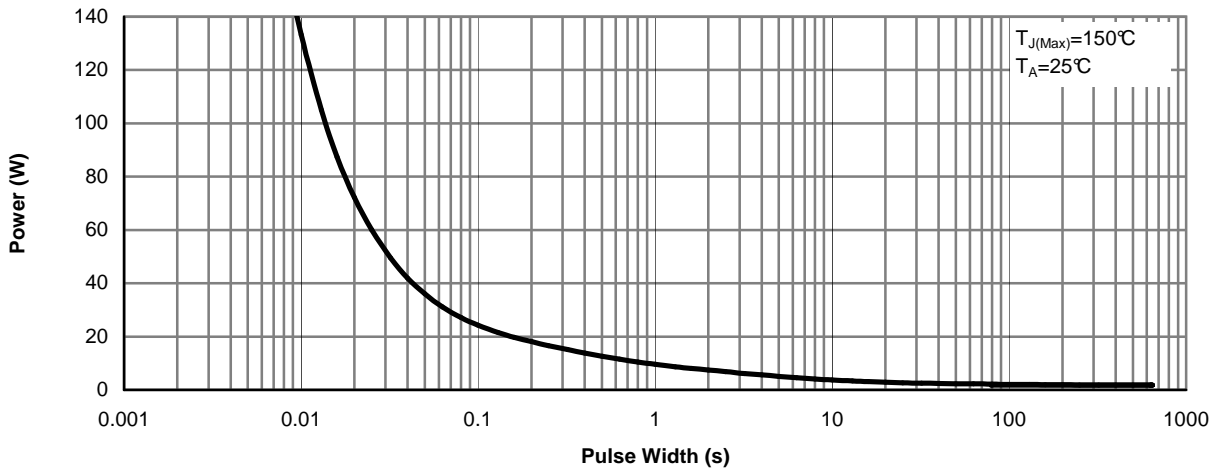
**Figure 8: Capacitance Characteristics**



**Figure 9: Single Pulse Avalanche Capability**



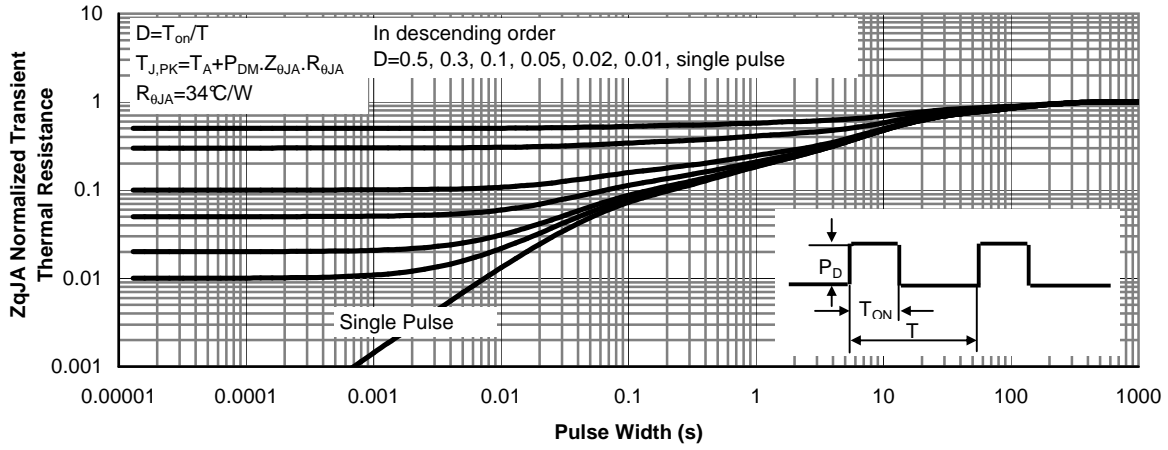
**Figure 10: Maximum Forward Biased Safe Operating Area (Note F)**



**Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note G)**

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**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



**Figure 12: Normalized Maximum Transient Thermal Impedance (Note G)**